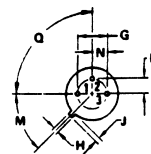
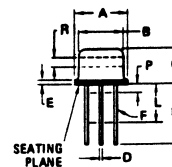


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ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

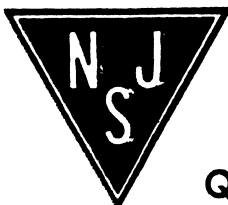
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Sustaining Voltage ($I_C = 5.0 \text{ mAdc}, I_B = 0$)	$V_{CE(sus)}$	20	—	—	Vdc
Collector-Emitter Sustaining Voltage (1) ($I_C = 5.0 \text{ mAdc}, R_{BE} = 10 \Omega$)	$V_{CER(sus)}$	40	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 15 \text{ Vdc}, I_B = 0$)	I_{CEO}	—	—	20	μAdc
Collector Cutoff Current ($V_{CE} = 15 \text{ Vdc}, V_{BE} = -1.5 \text{ V}, T_C = 150^\circ\text{C}$)	I_{CEX}	—	—	5.0	mAdc
Collector Cutoff Current ($V_{CE} = 35 \text{ Vdc}, V_{BE} = -1.5 \text{ V}$)		—	—	5.0	mAdc
Emitter Cutoff Current ($V_{BE} = 3.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	—	100	μAdc
ON CHARACTERISTICS					
DC Current Gain ($I_C = 360 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	5.0	—	—	—
($I_C = 50 \text{ mAdc}, V_{CE} = 15 \text{ Vdc}$)		40	—	120	—
DYNAMIC CHARACTERISTICS					
*Current-Gain – Bandwidth Product ($I_C = 50 \text{ mAdc}, V_{CE} = 15 \text{ Vdc}, f = 200 \text{ MHz}$)	f_T	1200	—	—	MHz
*Collector-Base Capacitance ($V_{CB} = 15 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$)	C_{cb}	—	1.8	3.5	pF
Noise Figure ($I_C = 10 \text{ mAdc}, V_{CE} = 15 \text{ Vdc}, f = 200 \text{ MHz}$) (Figure 2)	NF	—	3.0	—	dB
FUNCTIONAL TEST					
*Common-Emitter Amplifier Voltage Gain (Figure 1) ($I_C = 50 \text{ mAdc}, V_{CC} = 15 \text{ Vdc}, f = 50$ to 216 MHz)	G_{ve}	11	—	—	dB
*Power Input (Figure 2) ($I_C = 50 \text{ mAdc}, V_{CC} = 15 \text{ Vdc}, R_S = 50 \text{ ohms},$ $P_{out} = 1.26 \text{ mW}, f = 200 \text{ MHz}$)	P_{in}	—	—	0.1	mW

*Indicates JEDEC Registered Data.
(1) Pulsed thru a 25 mH Inductor; 50% Duty Cycle



STYLE 1
PIN 1. EMITTER
2. BASE
3. COLLECTOR

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.89	9.40	0.350	0.370
B	8.00	8.51	0.315	0.335
C	6.10	6.60	0.240	0.260
D	0.406	0.533	0.016	0.021
E	0.329	0.18	0.009	0.175
F	0.406	0.483	0.016	0.019
G	4.83	5.33	0.190	0.210
H	0.711	0.864	0.028	0.034
J	0.737	1.02	0.029	0.040
K	12.70	—	0.500	—
L	6.35	—	0.250	—
M	45°	NOM	45°	NOM
P	—	1.27	—	0.050
Q	—	90°	—	90°
R	2.54	—	0.100	—



Quality Semi-Conductors